Shantou Huashan Electronic Devices Co.,Ltd.

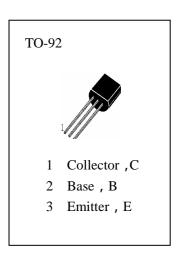
H337

SWITCHING AND AMPLFIER APPLICATIONS

Suitable for AF-Driver stages and low power output stages

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg} ——Storage Temperature55~150
T _j ——Junction Temperature150
P _C —Collector Dissipation
V _{CBO} ——Collector-Base Voltage50V
V _{CEO} ——Collector-Emitter Voltage45V
V _{EBO} ——Emitter-Base Voltage5V
I _C ——Collector Current800mA



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Тур	Max	Unit	Test Conditions
ВУсво	Collector-Base Breakdown Voltage	50			V	I _C =100 µ A, I _E =0
BVCEO	Collector-Emitter Breakdown Voltage	45			V	I _C =10mA, I _B =0
BVEBO	Emitter-Base Breakdown Voltage	5			٧	$I_{E}\!\!=\!\!100\muA$, $I_{C}\!\!=\!\!0$
ICES	Collector Cut-off Current		2	100	nA	$V_{CE}=45V, V_{BE}=0$
HFE	DC Current Gain	100		630		V _{CE} =1V, I _C =100mA
VCE(sat)	Collector- Emitter Saturation Voltage			0.7	٧	I _C =500mA, I _B =50mA
VBE(ON)	Base-Emitter On Voltage			1.2	V	V _{CE} =1V, I _C =300mA
fT	Current Gain-Bandwidth Product		100		MHz	V _{CE} =5V, I _C =10mA
Ccbo	Collector-Base Capacitance		12		pF	V_{CB} =10V, I_{E} =0 F=1MHz

hfe Classification

16	25	40	
100—250	160—400	250—630	

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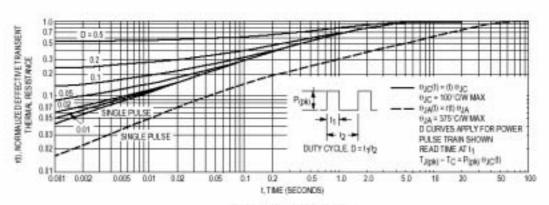


Figure 1. Thermal Response

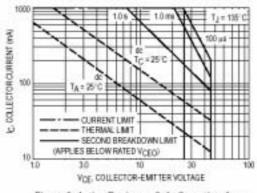


Figure 2. Active Region — Safe Operating Area

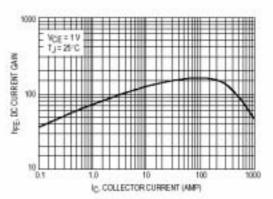


Figure 3. DC Current Gain

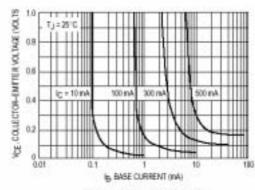


Figure 4. Saturation Region

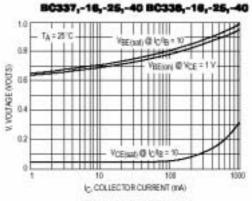


Figure 5. "On" Voltages

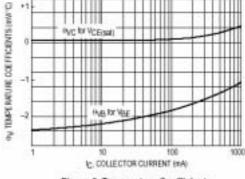


Figure 6. Temperature Coefficients

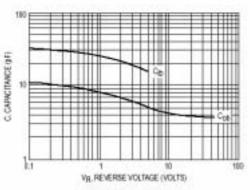


Figure 7. Capacitances